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BNS-OD-FC001/A4

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FEATURES

* 0.24 inch (6 mm) DIGIT HEIGHT * CONTINUOUS UNIFORM SEGMENTS * LOW POWER REQUIREMENT * EXCELLENT CHARACTERS APPEARANCE * HIGH BRIGHTNESS & HIGH CONTRAST * WIDE VIEWING ANGLE * SOLID STATE RELIABILITY

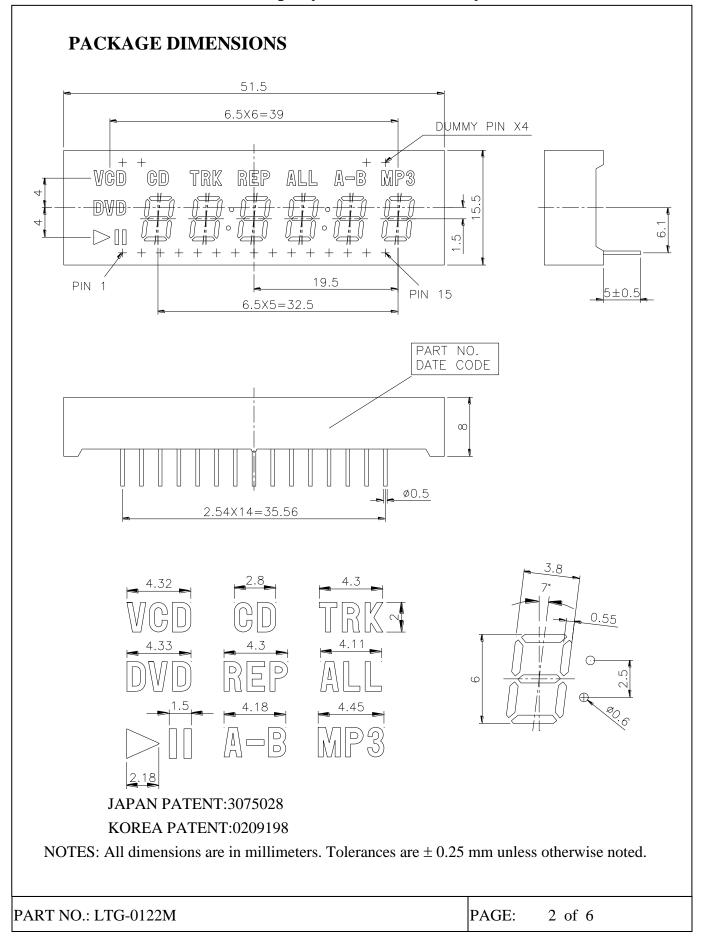
DESCRIPTION

The LTG-0122M is a 0.24 inch (6 mm) digit height 6 digit seven-segment display. The device is multi-color applicable display. The GREEN LED chips, which are made from GaP on GaP substrate and RED ORANGE LED chips, which are made from GaAsP on GaP. The device has a black face and white segments.

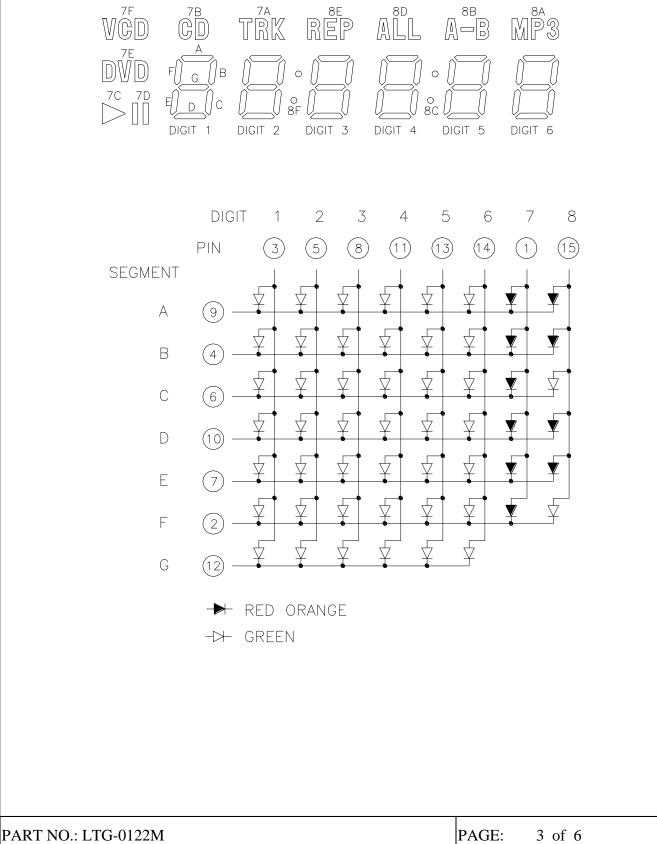
DEVICE

PART NO.	DESCRIPTION
GREEN & RED ORANGE	
LTG-0122M	Multiplex Common Anode

PART NO.: LTG-0122M







PIN CONNECTION

NO	CONNECTION
1	COMMON ANODE 7A~7F
2	CATHODE F
3	COMMON ANODE (DIGIT 1)
4	CATHODE B
5	COMMON ANODE (DIGIT 2)
6	CATHODE C
7	CATHODE E
8	COMMON ANODE (DIGIT 3)
9	CATHODE A
10	CATHODE D
11	COMMON ANODE (DIGIT 4)
12	CATHODE G
13	COMMON ANODE (DIGIT 5)
14	COMMON ANODE (DIGIT 6)
15	COMMON ANODE 8A~8F

PART NO.: LTG-0122M

ABSOLUTE MAXIMUM RATING

PARAMETER	GREEN	RED ORANGE	UNIT			
Power Dissipation Per Chip	75	75	mW			
Peak Forward Current Per Chip (Frequency 1Khz, 10% duty cycle)	100*	100*	mA			
Continuous Forward Current Per Chip	25	25	mA			
Derating Linear From 25°C Per Chip	0.33	0.33	mA/°C			
Reverse Voltage Per Chip	5	5	V			
Operating Temperature Range	-35°C to +85°C					
Storage Temperature Range	-35°C to +85°C					
Solder Temperature: max 260°C for max 3	soo at 1 6mm balow	sosting plana				

Solder Temperature: max 260°C for max 3sec at 1.6mm below seating plane

* see figure 5 to establish pulsed condition

ELECTRICAL / OPTICAL CHARACTERISTICS AT Ta=25°C

GREEN

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity Per Segment	Iv	500	1600		μcd	$I_F = 10 mA$
Peak Emission Wavelength	λp		565		nm	$I_F = 20 mA$
Spectral Line Half-Width	Δλ		30		nm	$I_F = 20 m A$
Dominant Wavelength	λd		569		nm	$I_F = 20 m A$
Forward Voltage Per Chip	VF		2.1	2.6	V	$I_F = 10 mA$
Reverse Current Per Chip	Ir			100	μΑ	$V_R = 5V$
Luminous Intensity Matching Ratio	Iv-m			2:1		$I_F = 10 mA$

RED ORANGE

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Sterance	Iv	500	1600		μcd	$I_F = 10 mA$
Peak Emission Wavelength	λp		630		nm	$I_F = 20 m A$
Spectral Line Half-Width	Δλ		40		nm	$I_F = 20 m A$
Dominant Wavelength	λd		621		nm	$I_F = 20 mA$
Forward Voltage Per Chip	VF		2	2.6	V	$I_F = 10 mA$
Reverse Current Per Chip	Ir			100	μΑ	$V_R = 5V$
Luminous Intensity Matching Ratio	Iv-m			2:1		$I_F = 10 mA$

Note: Luminous intensity is measured with a light sensor and filter combination that approximates

the CIE (Commision Internationale De L'Eclairage) eye-response curve.

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TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

